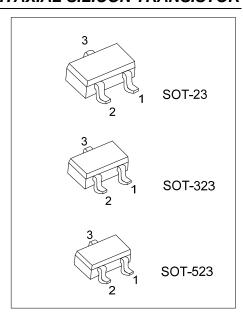
DTC124E

NPN EPITAXIAL SILICON TRANSISTOR

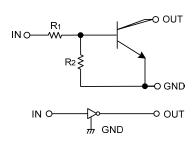
NPN DIGITAL TRANSISTOR (BUILT-IN RESISTORS)

FEATURES

- *Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors (see the equivalent circuit).
- *The bias resistors consist of thin-film resistors with complete isolation to allow positive biasing of the input They also have the advantage of almost completely eliminating parasitic effects.
- *Only the on / off conditions need to be set for operation, making device design easy.



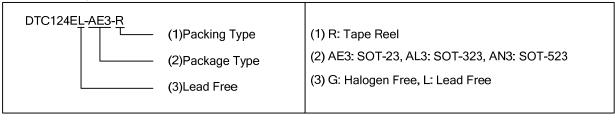
EQUIVALENT CIRCUIT



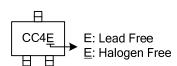
ORDERING INFORMATION

Ordering Number		Dookogo	Pin Assignment			Dacking	
Lead Free	Halogen Free	Package	1	2	3	Packing	
DTC124EL-AE3-R	DTC124EG-AE3-R	SOT-23	G	I	0	Tape Reel	
DTC124EL-AL3-R	DTC124EG-AL3-R	SOT-323	G	I	0	Tape Reel	
DTC124EL-AN3-R	DTC124EG-AN3-R	SOT-523	G	I	0	Tape Reel	

Note: Pin Assignment: G: GND I: IN O: OUT



MARKING



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■ ABSOLUATE MAXIUM RATINGS (T_A = 25°C, unless otherwise specified.)

PARAMETER		SYMBOL	RATINGS	UNIT	
Supply Voltage		V_{CC}	50	V	
Input Voltage		V_{IN}	-10 ~ +40	V	
Output Current		Ic	100	Л	
		lo	30	mA	
Power Dissipation	SOT-23/SOT-323	ם	200	mW	
	SOT-523	P_D	150		
Junction Temperature		T_J	150	$^{\circ}\!\mathbb{C}$	
Storage Temperature		T _{STG}	-40 ~ +150	$^{\circ}\!\mathbb{C}$	

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ ELECTRICAL CHARACTERISTICS (T_A= 25°C)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Input Voltage	$V_{I(OFF)}$	V _{CC} = 5V, I _{OUT} =100μA			0.5	V
	$V_{I(ON)}$	V _{OUT} = 0.2V, I _{OUT} = 5mA	3			V
Output Voltage	$V_{O(ON)}$	I _{OUT} /I _{IN} = 10mA / 0.5 mA		0.1	0.3	V
Input Current	I _I	V _{IN} = 5V			0.36	mA
Output Current	I _{O(OFF)}	V _{CC} = 50V , V _{IN} =0V			0.5	μΑ
DC Current Gain	Gı	V _{OUT} = 5V, I _{OUT} = 5mA	56			
Input Resistance	R1		15.4	22	28.6	kΩ
Resistance Ratio	R2/R1		8.0	1	1.2	
Transition Frequency	f_T	V_{CE} =10V, I_E = -5mA, f=100MHz (Note)		250		MHz

Note: Transition frequency of the device

■ TYPICAL CHARACTERICS

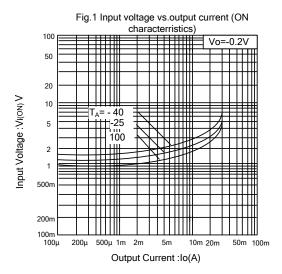
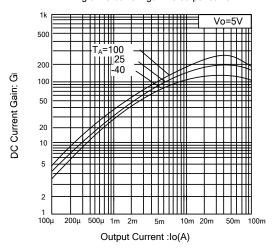


Fig.3 DC current gain vs.output current



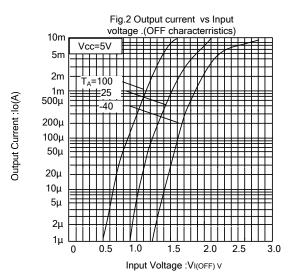
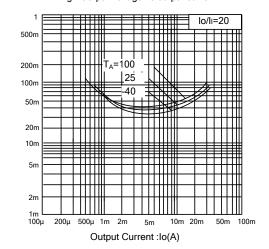


Fig.4Output voltage vs.output current



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Output Voltage: Vo(on) V